

Au cœur de l'efficacité énergétique



ElectroMagnetic Compatibility in Power Electronics: from packaging to EMC filter optimization

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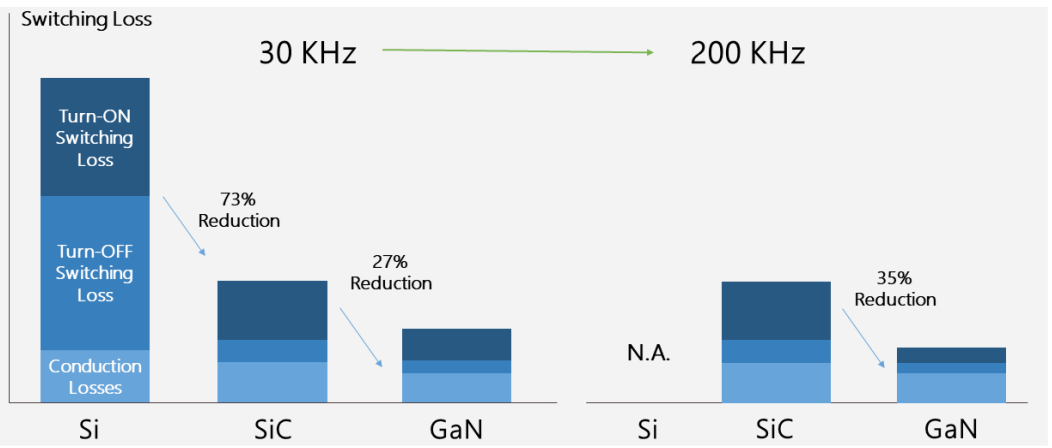


Clustering and Global Challenges
(CGC2021)

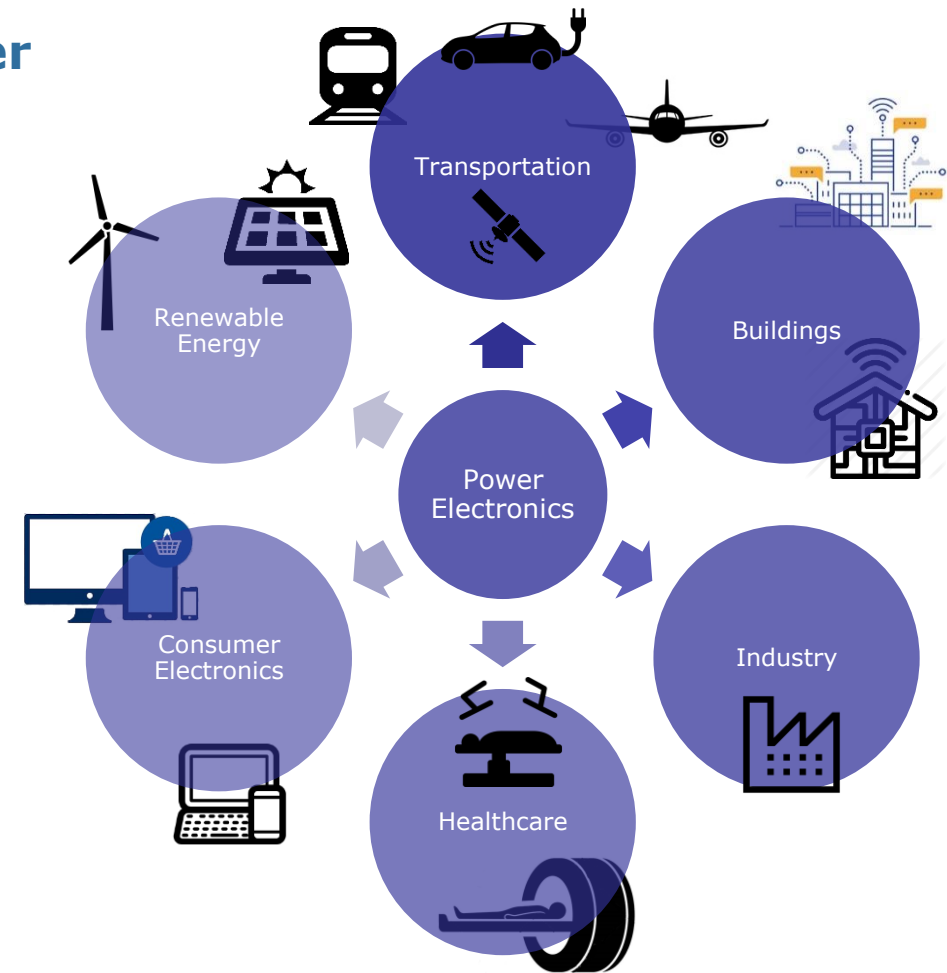


Introduction

- 40% of electricity processed by power electronics
- Expected doubling over the next decade, reaching up to 80% by 2030
- Impact of Wide Bandgap revolution



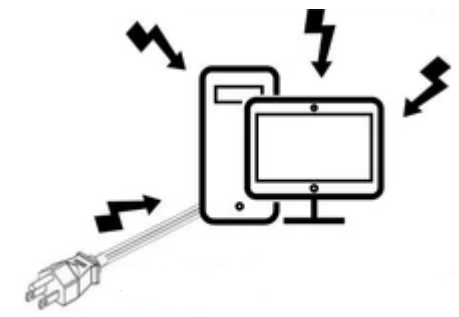
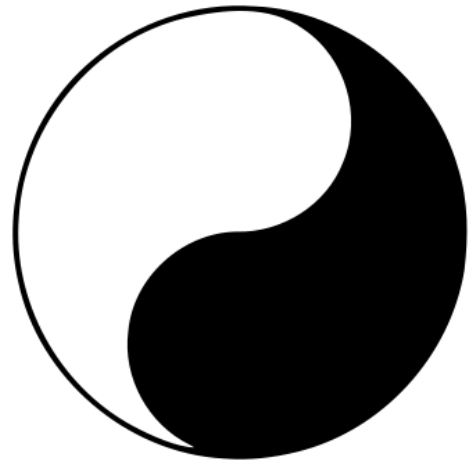
Spec Consortium, Singapore



Introduction

Switched Mode Power Supply

- **High efficiency**
- **Low volume, weight**
- **High dynamic**



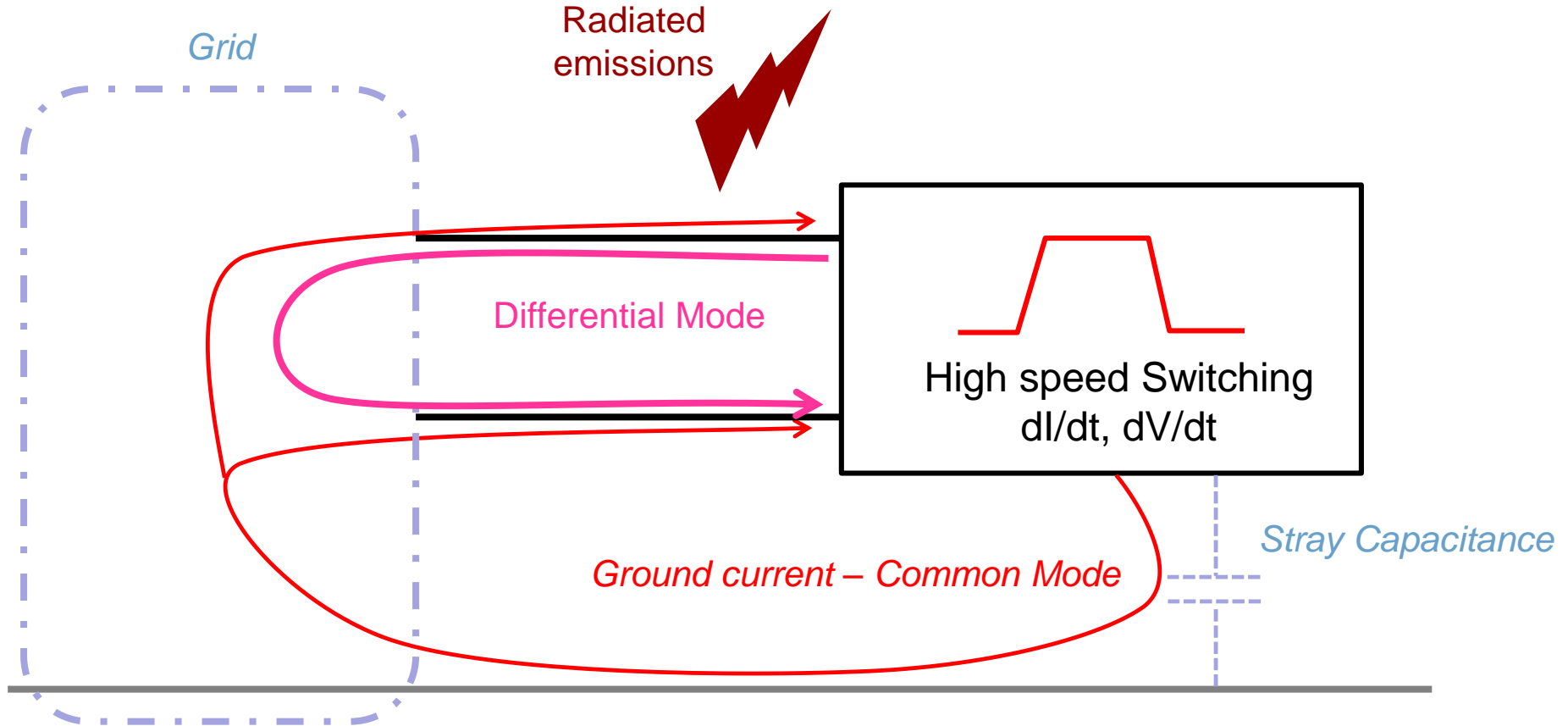
- **Electromagnetic Interferences**

Outline

- 1. EMI generation principle**
- 2. EMC & Semiconductor Packaging**
- 3. EMC Filter design and optimization**
- 4. EMC models at system level**

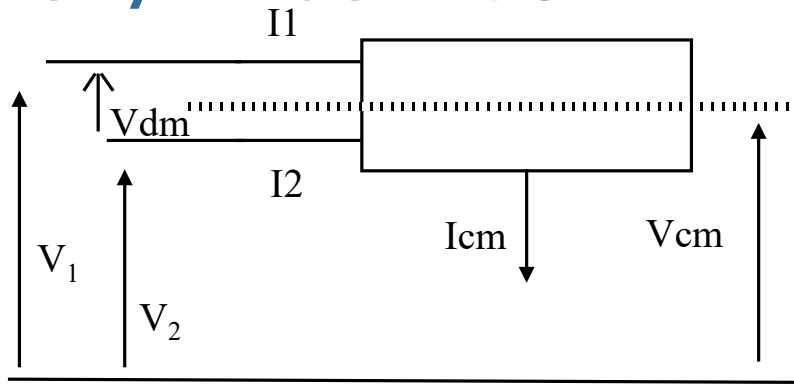
EMC: ElectroMagnetic Compatibility
EMI: ElectroMagnetic Interferences

1. EMI Generation Principle



1. EMI Generation Principle

CM/DM definition



$$V_{dm} = V_1 - V_2$$

$$V_{cm} = \frac{V_1 + V_2}{2}$$

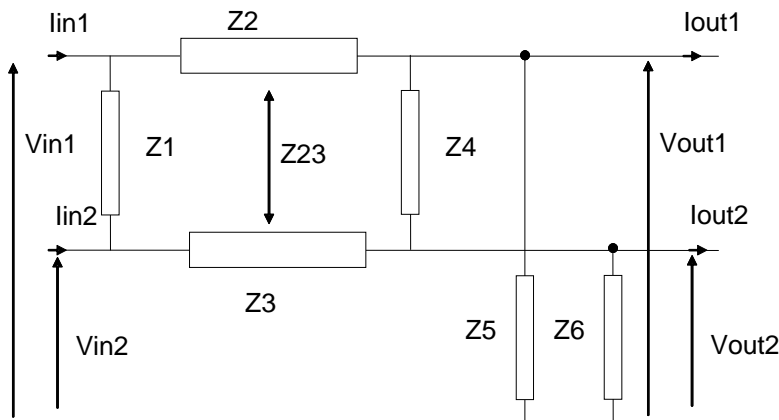
$$I_{dm} = \frac{I_1 - I_2}{2}$$

$$I_{cm} = I_1 + I_2$$

$$\begin{bmatrix} V_{md} \\ I_{md} \\ V_{mc} \\ I_{mc} \end{bmatrix}_{in/out} = [P] \cdot \begin{bmatrix} V_1 \\ V_2 \\ I_1 \\ I_2 \end{bmatrix}_{in/out}$$

$$[P] = \begin{bmatrix} 1 & -1 & 0 & 0 \\ 0 & 0 & \frac{1}{2} & \frac{-1}{2} \\ \frac{1}{2} & \frac{1}{2} & 0 & 0 \\ 0 & 0 & 1 & 1 \end{bmatrix}$$

CM/DM independence if symmetry



$$\begin{bmatrix} V_1 \\ V_2 \\ I_1 \\ I_2 \end{bmatrix}_{out} = [Mat] \cdot \begin{bmatrix} V_1 \\ V_2 \\ I_1 \\ I_2 \end{bmatrix}_{in}$$

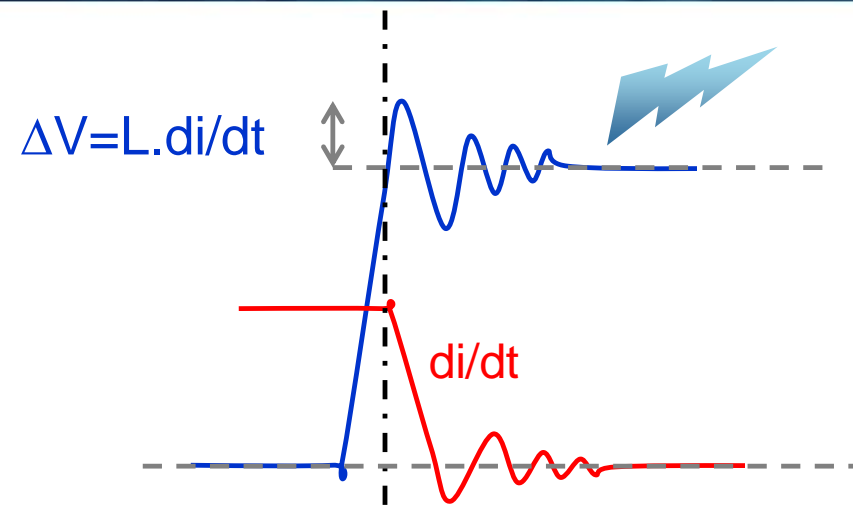
$$\begin{bmatrix} V_{md} \\ I_{md} \\ V_{mc} \\ I_{mc} \end{bmatrix}_{out} = [P] \cdot [Mat] \cdot [P]^{-1} \cdot \begin{bmatrix} V_{md} \\ I_{md} \\ V_{mc} \\ I_{mc} \end{bmatrix}_{in}$$

If Z2=Z3
And Z5=Z6

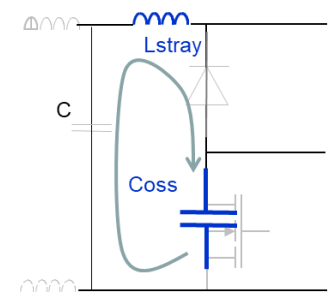
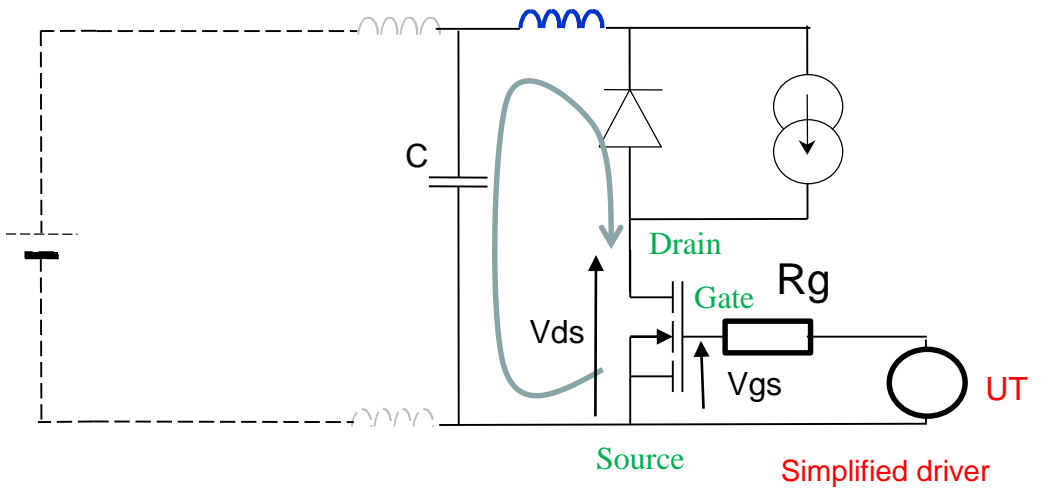
DM	0
0	CM

2. EMC & Semiconductor Packaging

Stray inductance: Voltage overshoot & ringing



Stray inductance (switching loop)



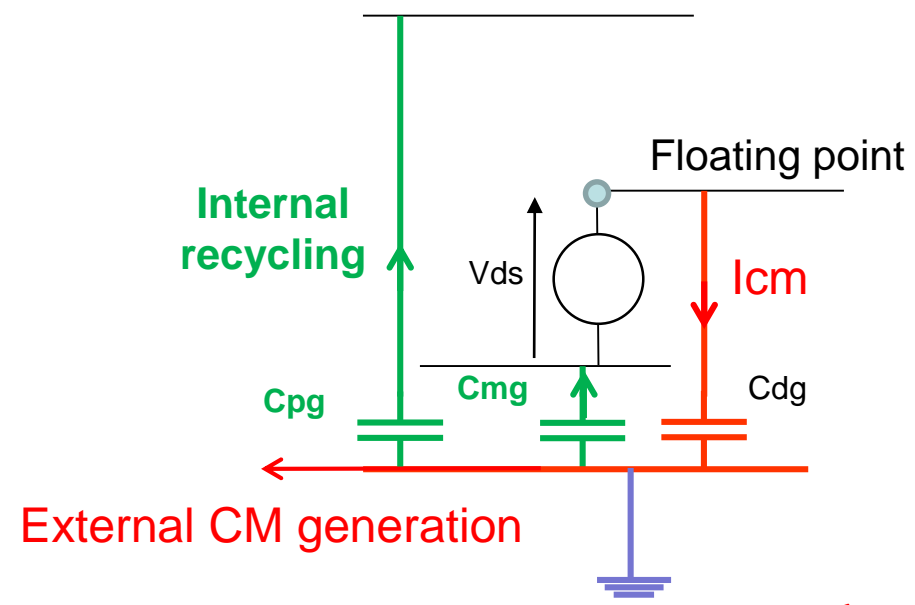
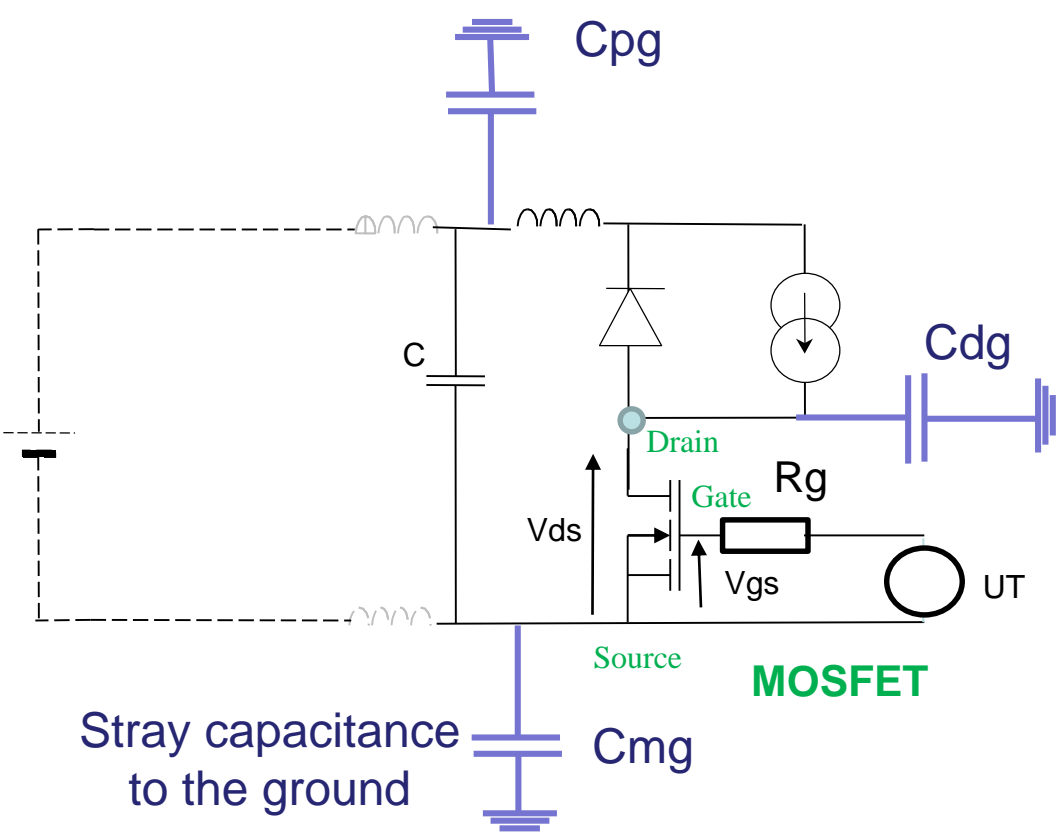
$$z = R/2 \cdot \sqrt{C_{oss}/L_{stray}}$$

Reduced ΔV : $50A/ns \cdot 5nH \rightarrow 250V!$
 Increased damping

Nano- or Subnano-henry requirements

2. EMC & Semiconductor Packaging

- **Stray capacitances & CM generation**



**Reduce C_{dg} ,
increase C_{pg} , C_{mg}**

2. EMC & Semiconductor Packaging

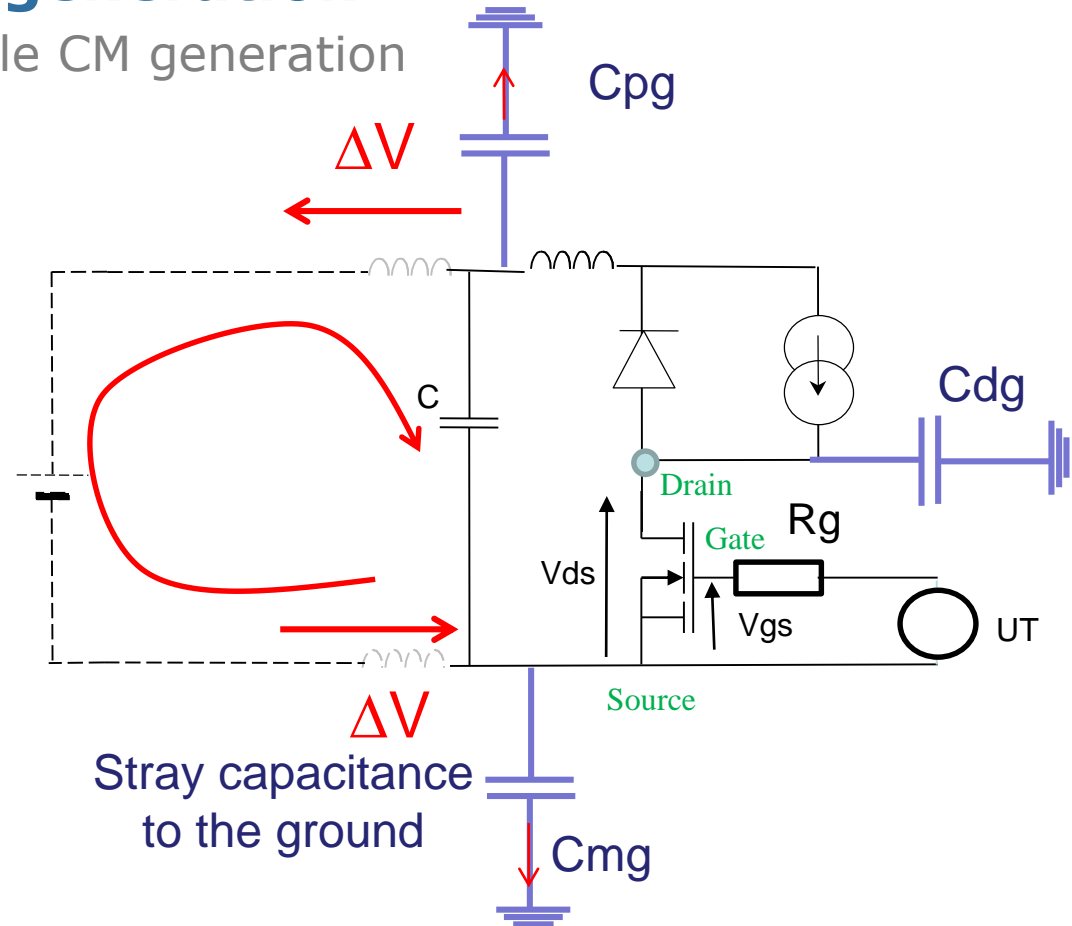
• Stray capacitances & CM generation

- Warning: if $C_{pg} \neq C_{mg}$: possible CM generation

$$I_{cpg} = C_{pg} \frac{d\Delta V}{dt} = -I_{cmg}$$

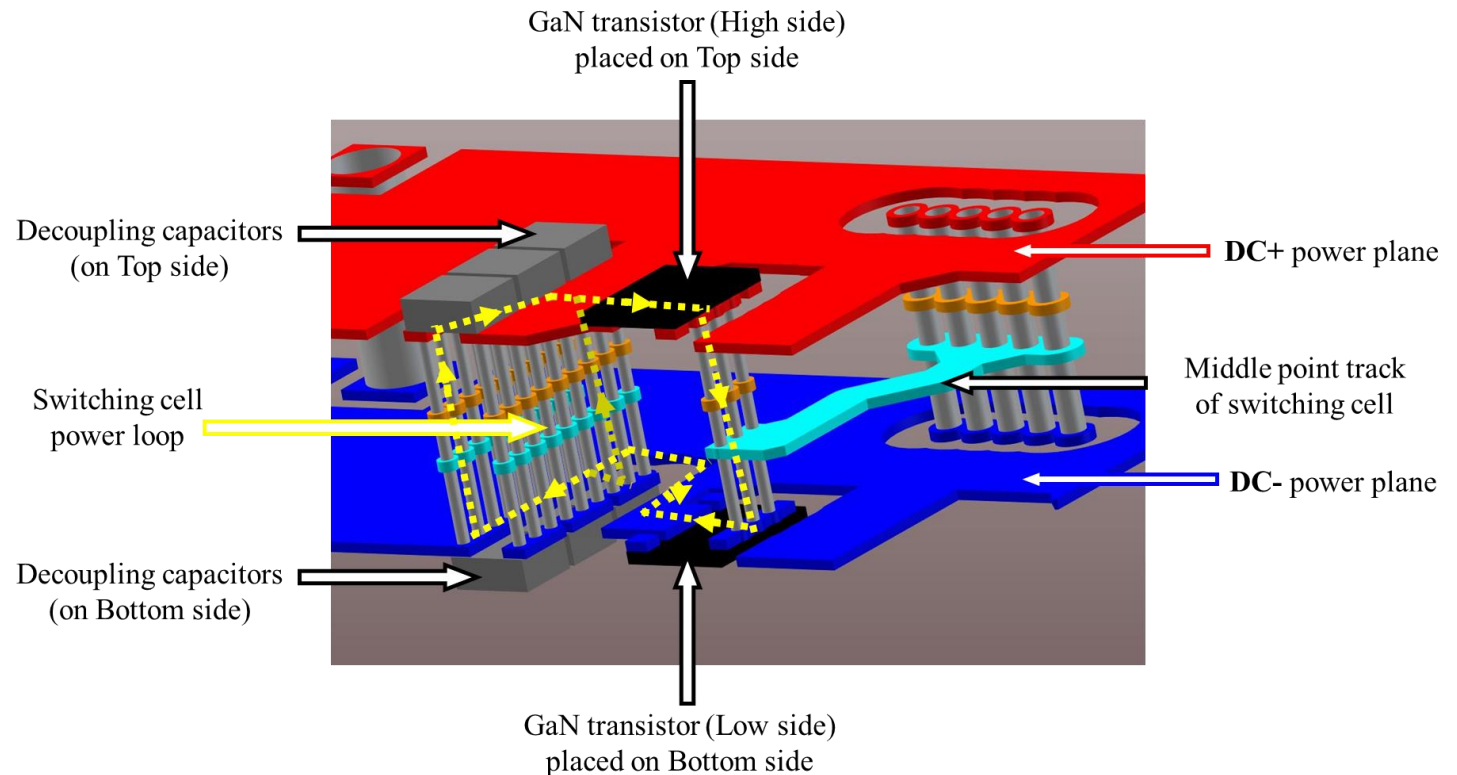
Only if $C_{pg} = C_{mg}$

Keep symmetry



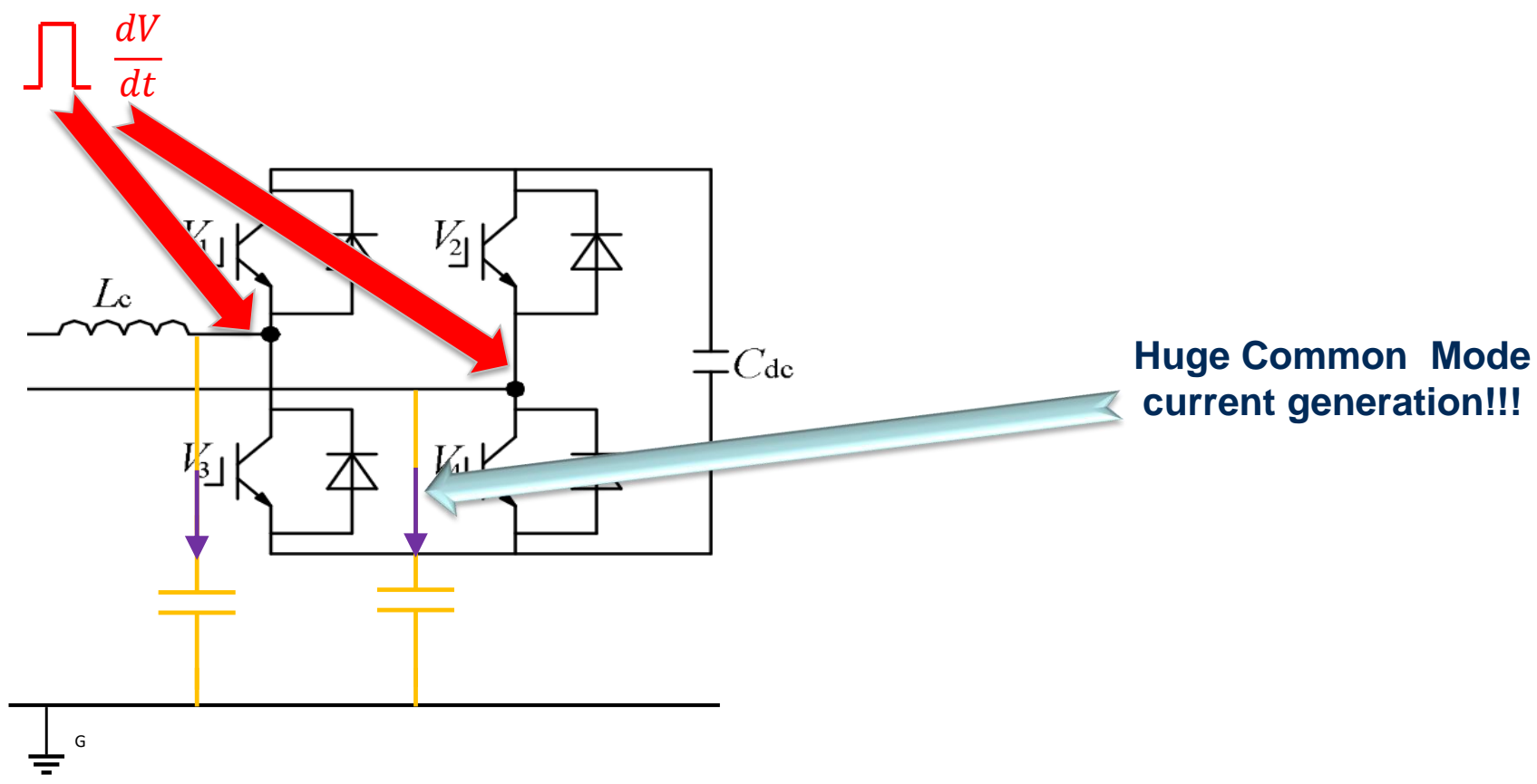
2. EMC & Semiconductor Packaging

Example of G2ELab recent result: Power Chip on Chip applied to GaN devices



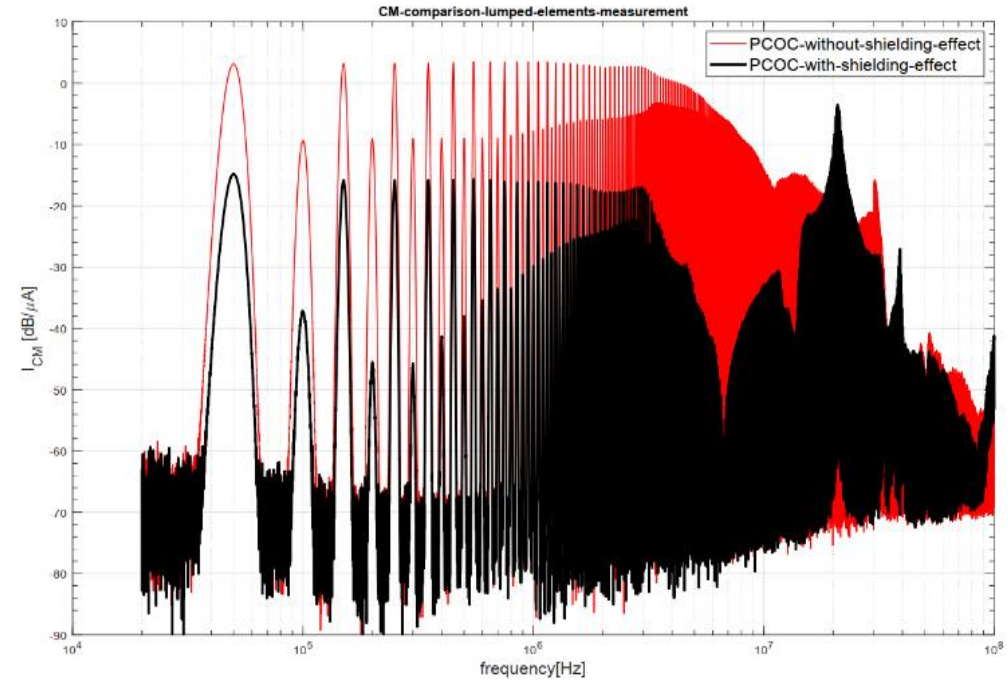
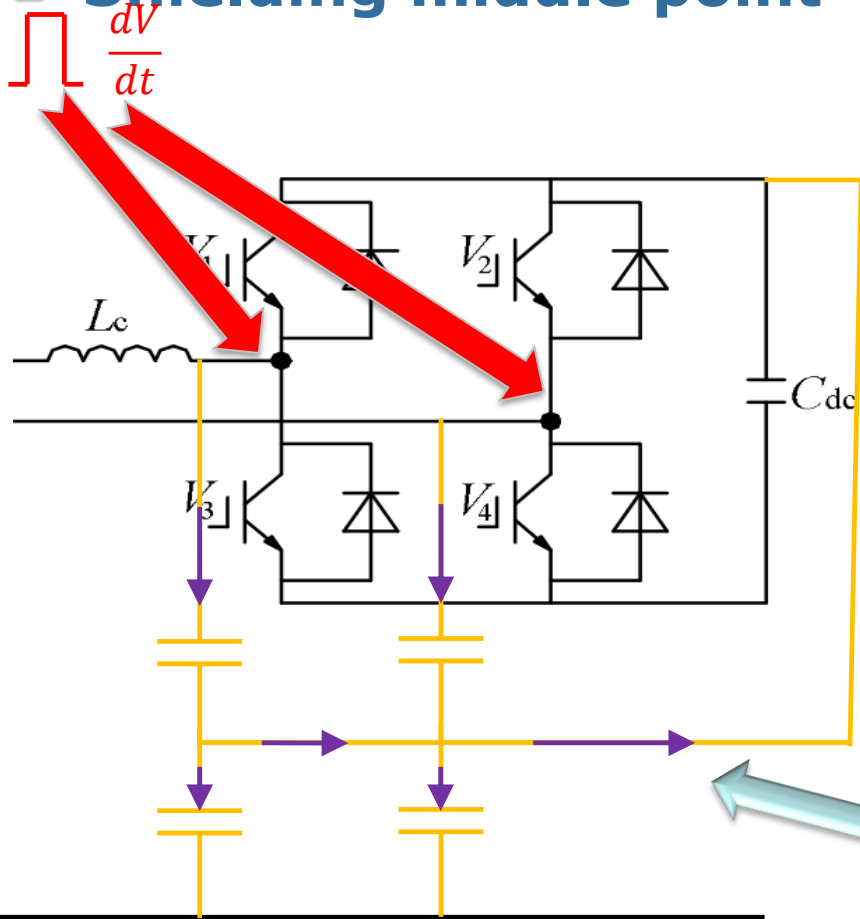
2. EMC & Semiconductor Packaging

Shielding middle point



2. EMC & Semiconductor Packaging

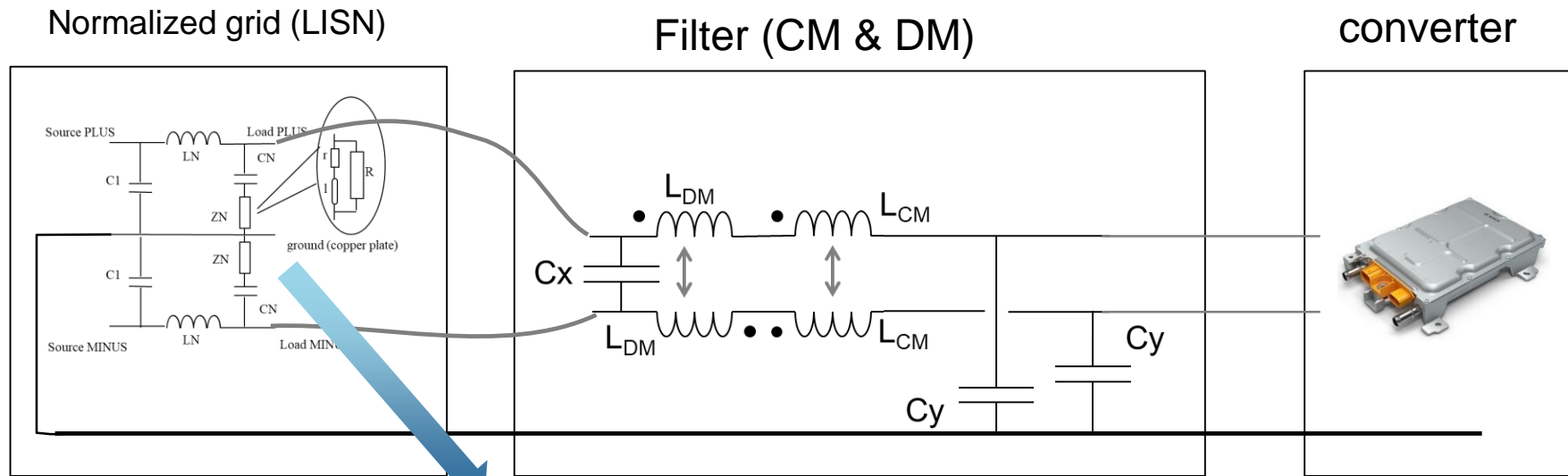
Shielding middle point



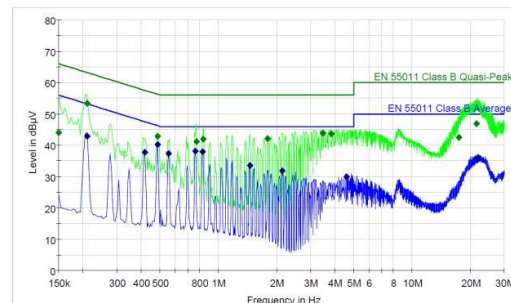
Most of Common Mode current is recirculating inside converter

3. EMC Filter design and optimization

■ Design by optimization of EMC Filter

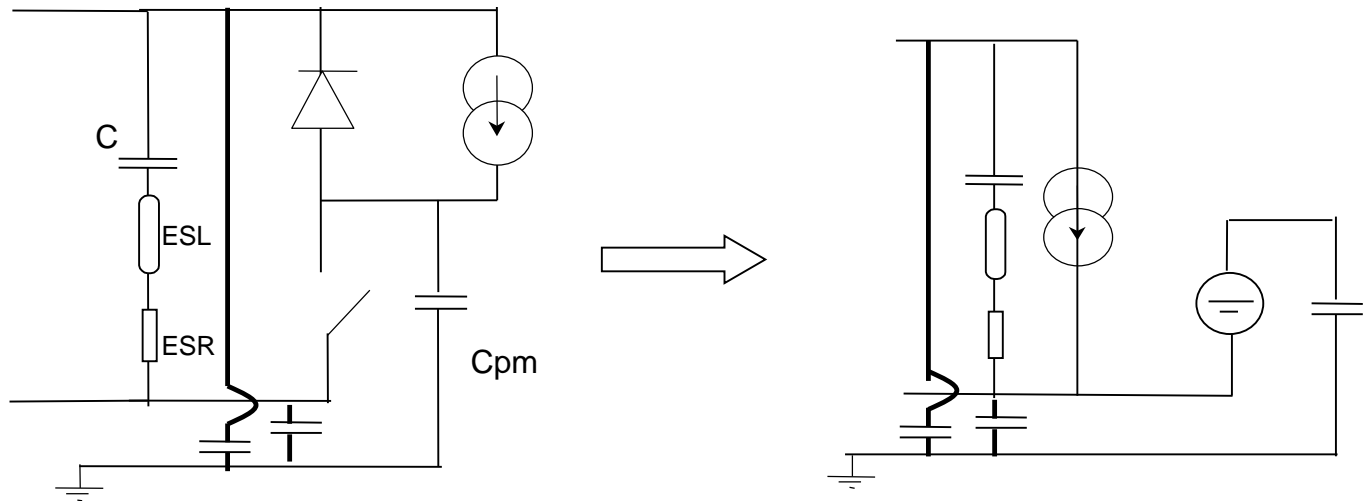


Line-Ground Voltage monitored



3. EMC Filter design and optimization

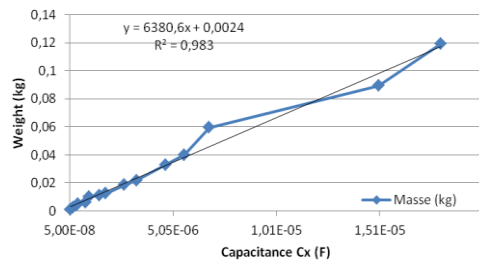
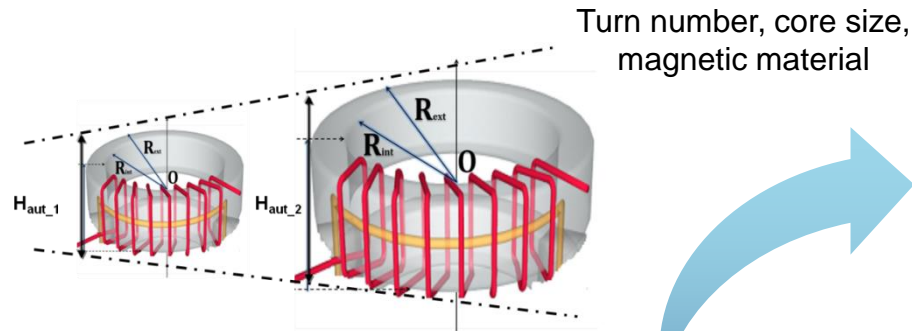
■ Design by optimization of EMC Filter: Frequency model of the converter



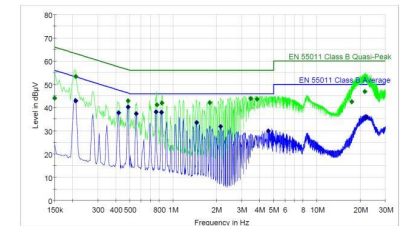
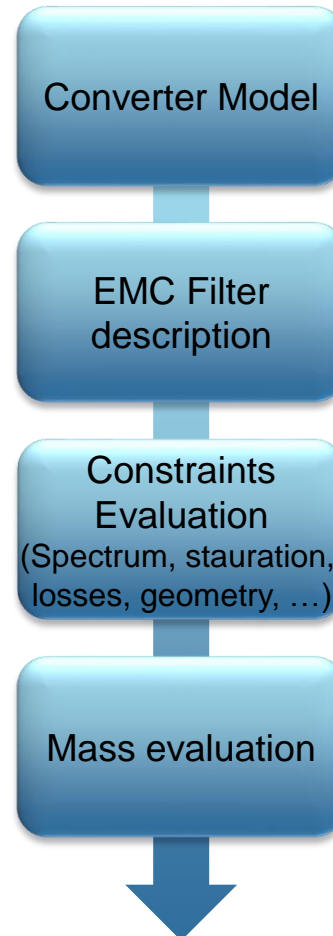
1 current source: current discontinuity
1 voltage source: voltage swing

3. EMC Filter design and optimization

Design by optimization of EMC Filter: Design Methodology

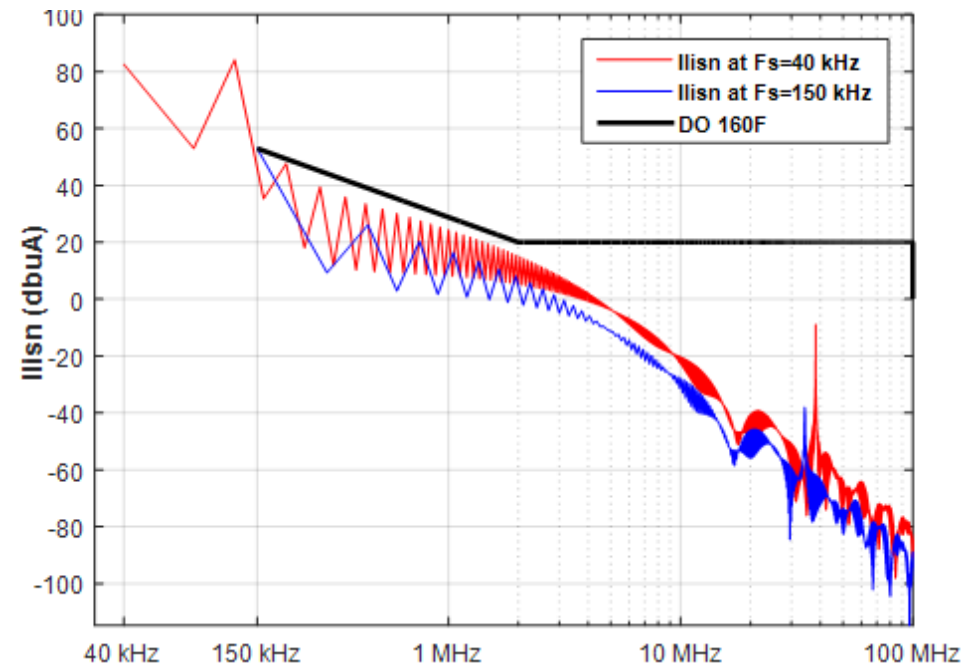
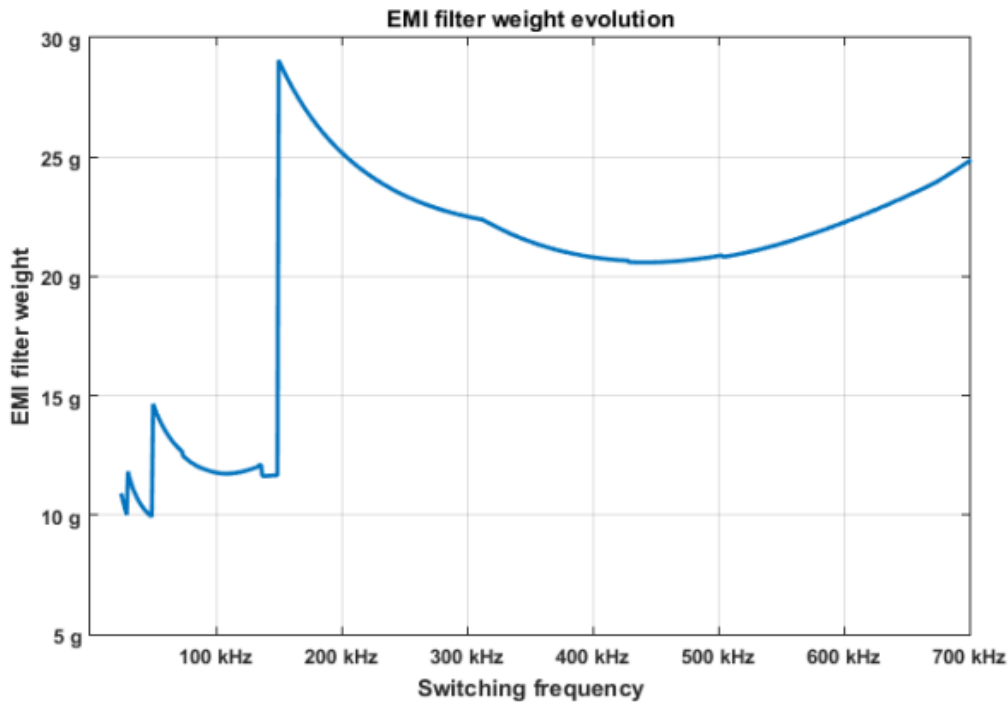


Datasheet interpolation for capacitors



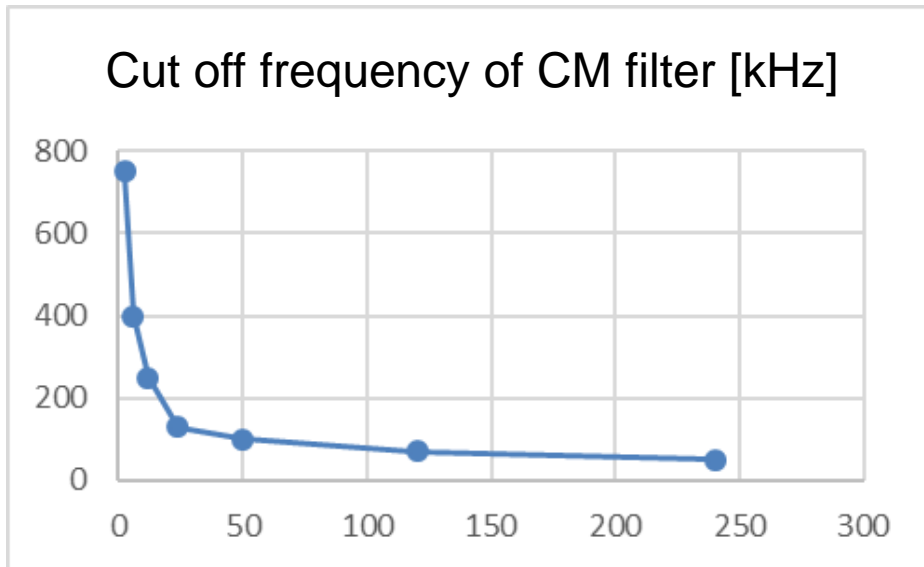
3. EMC Filter design and optimization

■ Design by optimization of EMC Filter: impact of Fsw

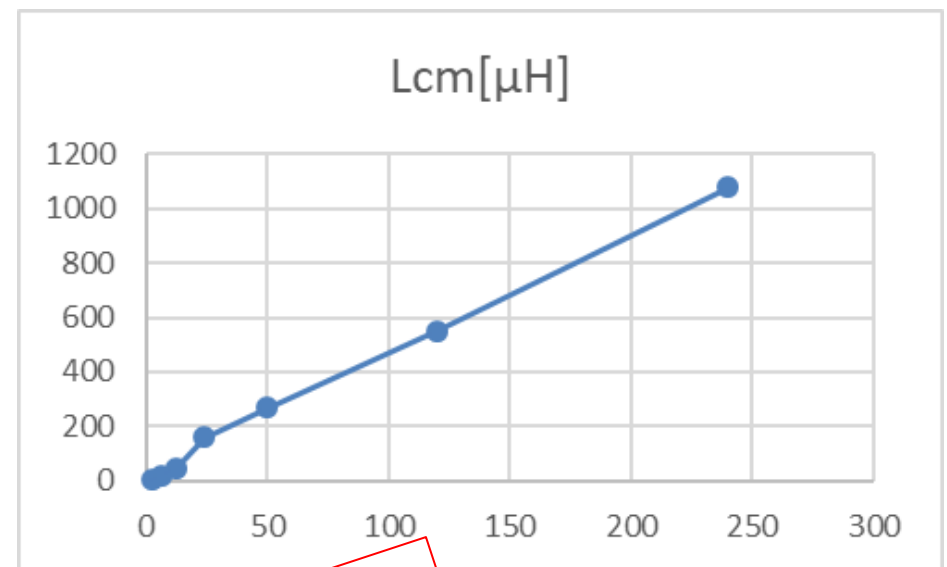


3. EMC Filter design and optimization

■ Design by optimization of EMC Filter: impact of floating point capacitance on the filter



Cpm[pF]

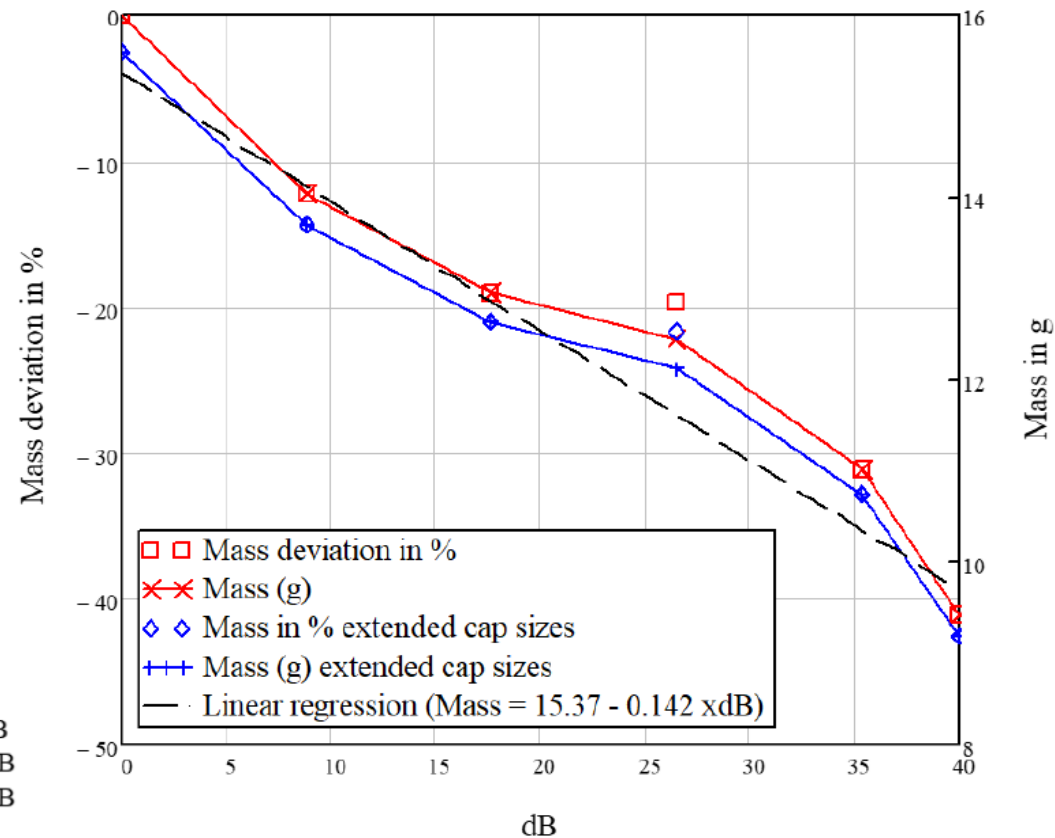
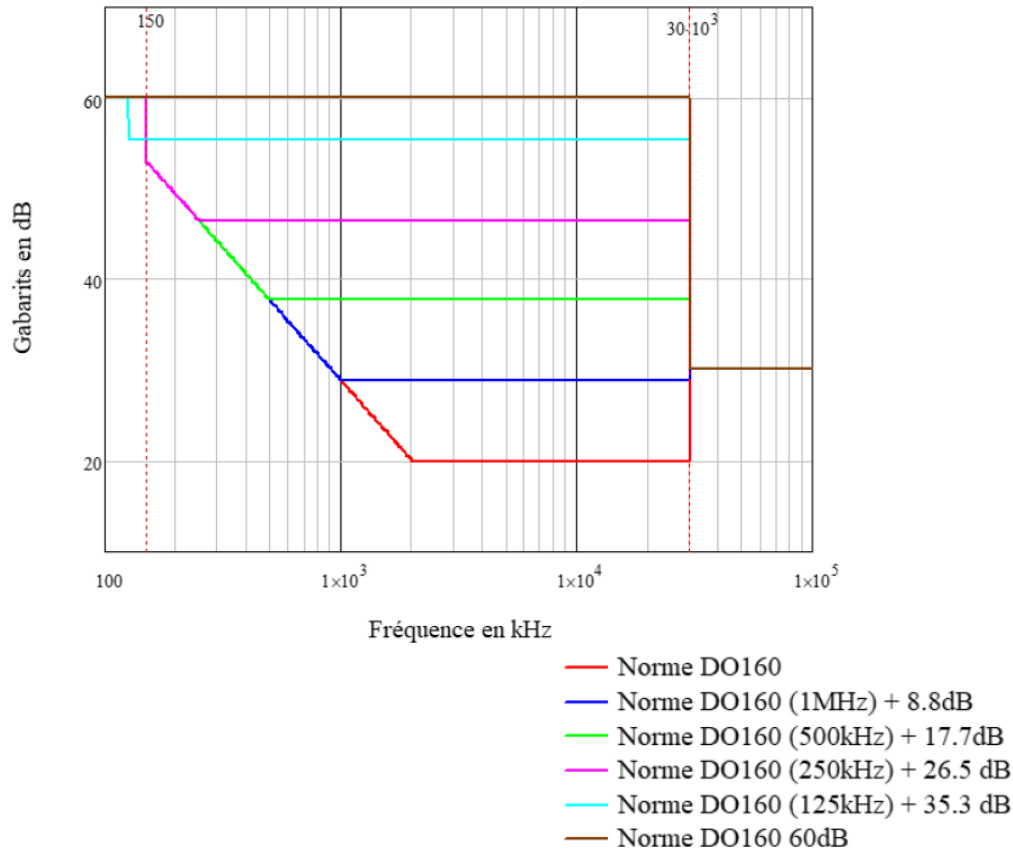


Cpm[pF]

Reducing EMI at packaging level

3. EMC Filter design and optimization

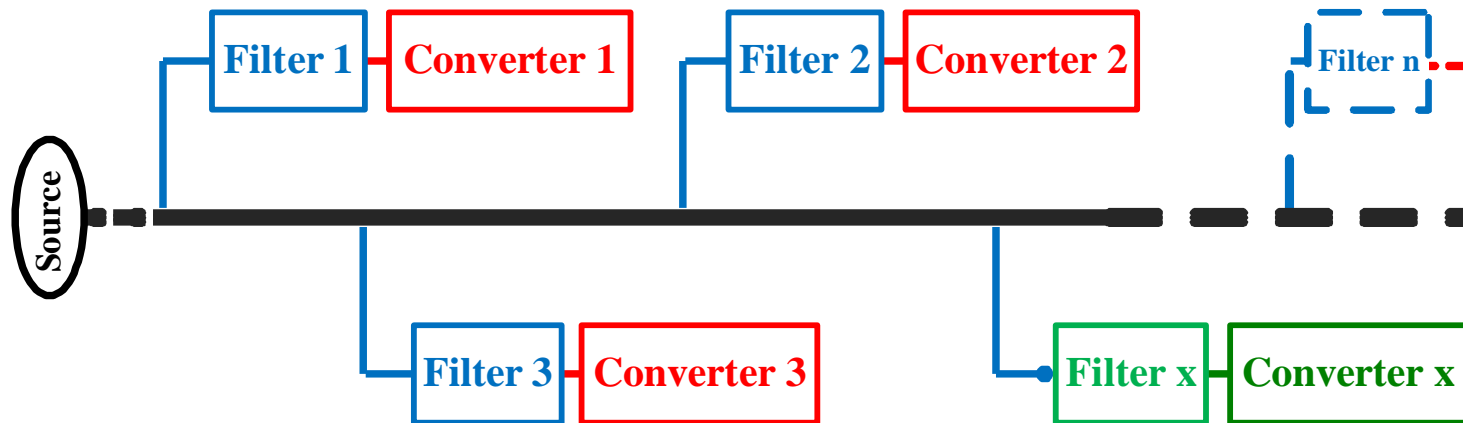
Variation of standard (DO160)



4. EMC models at system level

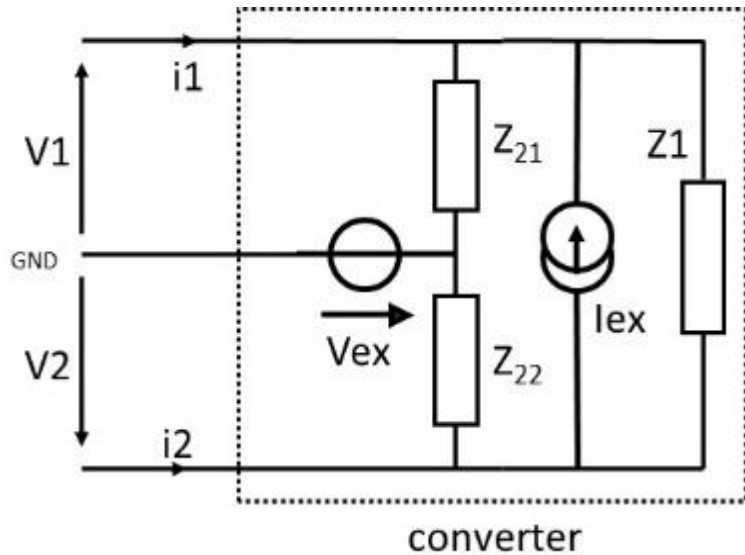
- Usual EMC approach: standardized grid (LISN) and standardized emission level
- System optimization: real grids, computation of EMI level, comparison with disturbance level

Need of EMC models at system level

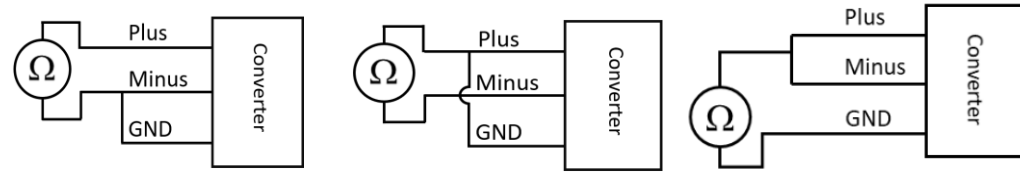


4. EMC models at system level

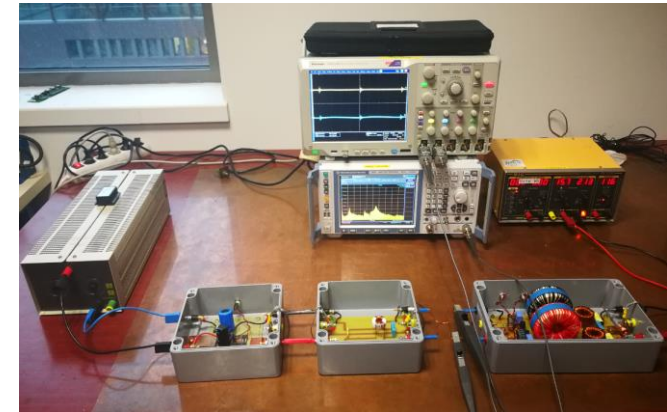
Black Box / Terminal Model



Identification process



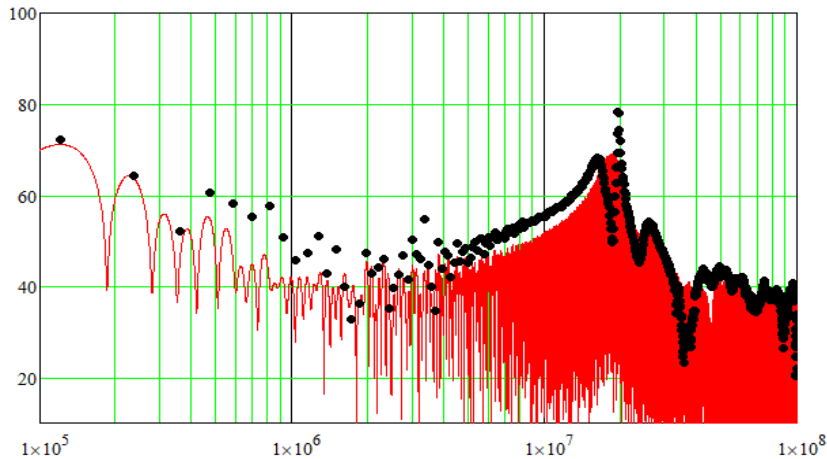
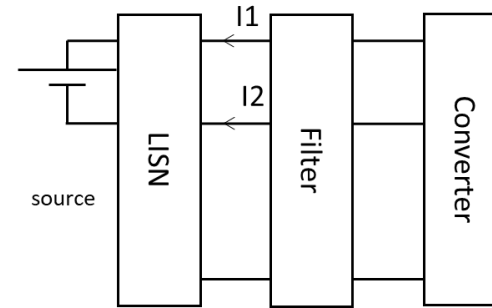
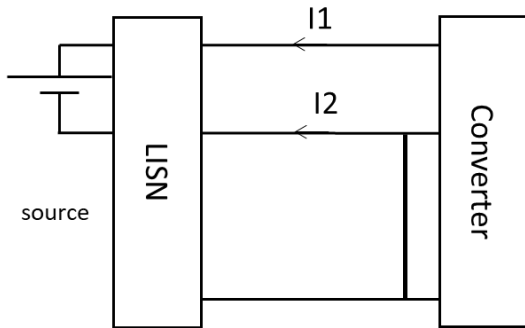
Off-line impedance measurement



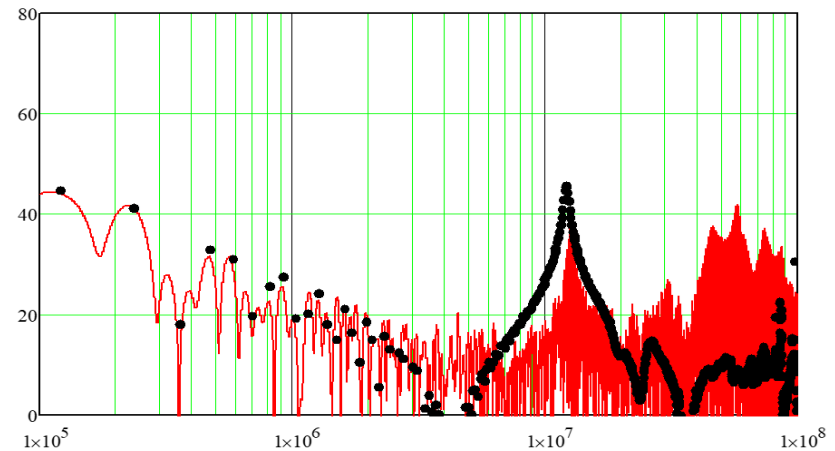
Line current measurement in a known configuration (LSIN)

4. EMC models at system level

Model validation in several configurations (exp results)



I1 – Minus to ground



I2 – EMC Filter

Conclusion

- **EMC as "dark side of Power Electronics"**
- **Wide Bandgap devices leads EMC issue more critical**
- **EMI reduction at packaging level**
 - Subnanohenry requirement
 - Reduced Floating Point capacitance, local shielding
 - Symmetry
- **EMC filter optimization**
 - Not straightforward phenomena
 - Technologically dependent
 - Proposed Design by Optimization methodology allows various studies (impact of technology, standards, ...)
- **EMC model at system level**
 - Future challenge of embedded grids ?